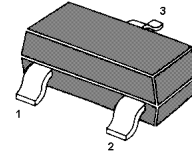
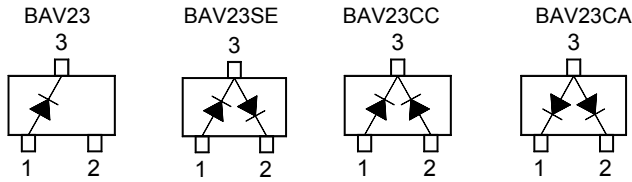


BAV23 / SE / CC / CA

Silicon Epitaxial Planar Diodes

High voltage switching diode



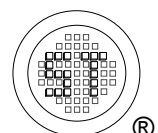
BAV23 Marking Code: **HC**
BAV23SE Marking Code: **PY**
BAV23CC Marking Code: **PZ**
BAV23CA Marking Code: **RA**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	250	V
Reverse Voltage	V_R	200	V
Forward Current	I_F	225	mA
Maximum Forward Current	I_{FM}	400	mA
Repetitive Peak Forward Current	I_{FRM}	625	mA
Non-repetitive Peak Forward Surge Current at $t = 10\text{ ms}$ at $t = 100\text{ }\mu\text{s}$ at $t = 1\text{ }\mu\text{s}$	I_{FSM}	1.7 3 9	A
Power Dissipation	P_{tot}	350	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	250	-	V
Forward Voltage at $I_F = 100\text{ mA}$ at $I_F = 200\text{ mA}$	V_F	- -	1 1.25	V
Reverse Current at $V_R = 200\text{ V}, T_J = 25^\circ\text{C}$ at $V_R = 200\text{ V}, T_J = 150^\circ\text{C}$	I_R	- -	100 100	nA μA
Total Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$	C_{tot}	-	5	pF
Reverse Recovery Time at $I_F = I_R = 30\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\text{ }\Omega$	t_{rr}	-	50	ns



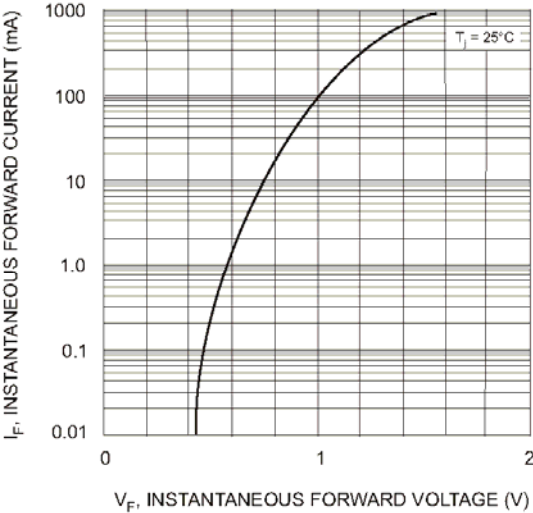


Fig. 1 Forward Characteristics

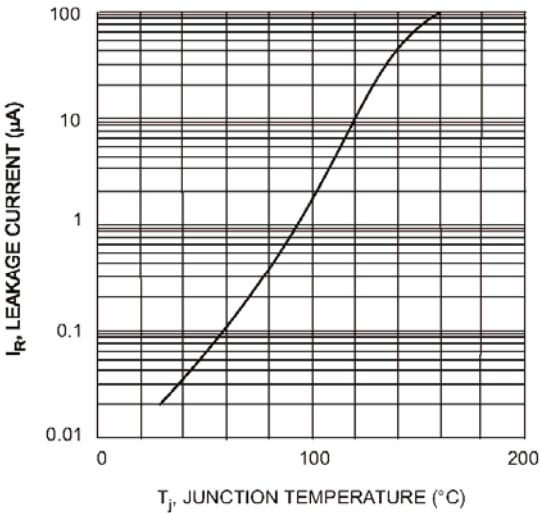
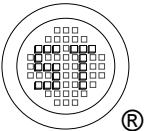
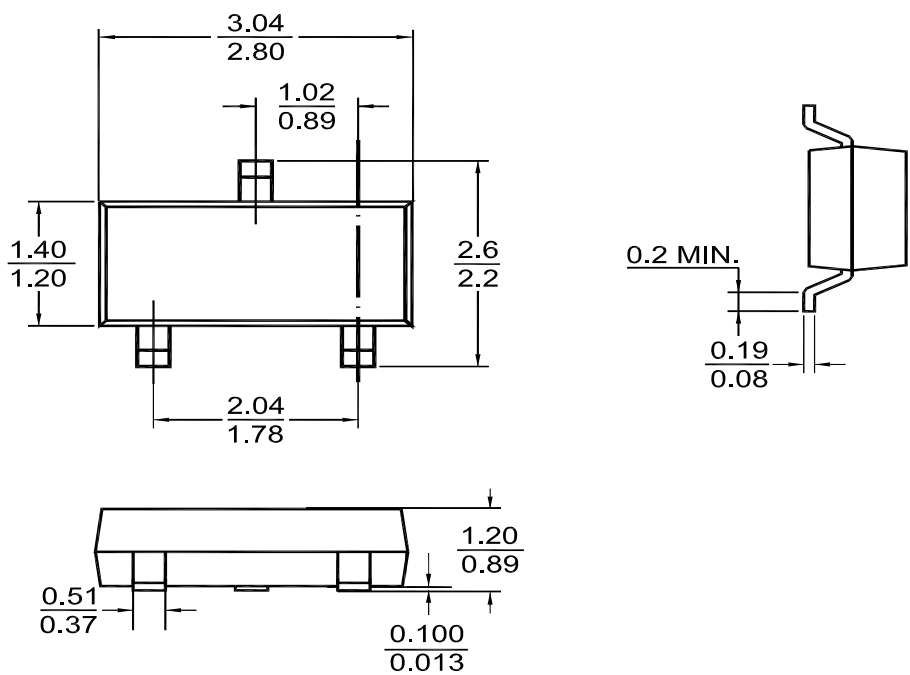


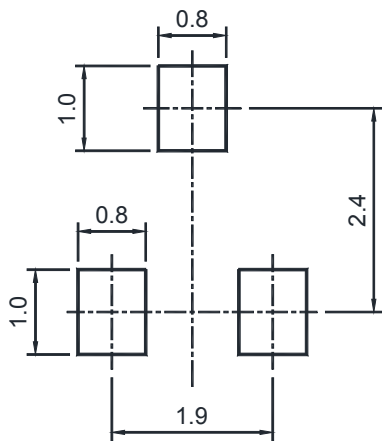
Fig. 2 Leakage Current vs Junction Temperature



PACKAGE OUTLINE(Dimensions in mm)



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

